ON Semiconductor

FINAL PRODUCT/PROCESS CHANGE NOTIFICATION #16893

Generic Copy

Issue Date: 29-Aug-2012

TITLE: Final Notification for Transfer of the NPN High Voltage Bipolar Power devices from ON Semiconductor ZR Fab in Phoenix (USA) to ON Semiconductor ISMF Fab in Seremban (Malaysia).

PROPOSED FIRST SHIP DATE: 29-Nov-2012

AFFECTED CHANGE CATEGORY(S): ON Semiconductor Fab Site

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:
Contact your local ON Semiconductor Sales Office or Product Engineer Farrah Omar <farrah.omar@onsemi.com>

SAMPLES: Contact your local ON Semiconductor Sales Office

ADDITIONAL RELIABILITY DATA: Available
Contact your local ON Semiconductor Sales Office or Laura Rivers <laura.rivers@onsemi.com>

NOTIFICATION TYPE:

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <quality@onsemi.com>.

DESCRIPTION AND PURPOSE:

ON Semiconductor is notifying customers of its plan to transfer High Voltage Bipolar Power devices from ON Semiconductor ZR Fab in Phoenix (USA) to ON Semiconductor ISMF Fab in Seremban (Malaysia).

The ISMF facility is an ON Semiconductor owned Wafer Fab that has been producing products for ON Semiconductor since 1998. Several existing technologies within ON Semiconductor's product families are currently sourced from ISMF. ON Semiconductor Seremban Wafer Fab are TS16949, ISO-9001 and ISO-14000 certified.

Qualification tests are designed to show that the reliability of transferred devices will continue to meet or exceed ON Semiconductor standards.

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RELIABILITY DATA SUMMARY:

Reliability testing was performed on qualification vehicles chosen based on die size, voltage rating, and run rates.

Reliability Test Results:

MJE18008G

Test:	Conditions:	Interval:	Results
HTRB	Ta=150℃,80% Rated Voltage	1008 hrs	0/240
Autoclave	Ta=121℃ RH=100% ~15 psig	96 hrs	0/240
HTSL	Ta = 150℃	1008 hrs	0/240
H3TRB	Ta=85℃ RH=85% bias=80% rated V or 100V Max	1008 hrs	0/240
IOL	Ta=25℃, Delta TJ = 100℃, Ton/off = 2 min.	8572 cycles	0/240
TC	Ta= -65℃ to 150℃	1000 cycles	0/240
RSH	Ta=260C, 10 sec dwell		0/90

ELECTRICAL CHARACTERISTIC SUMMARY:

Available upon request

CHANGED PART IDENTIFICATION:

Devices marked with date code A248 (A=Assembly site designator) and greater may have Die from either the ISMF Fab in Seremban (Malaysia) or the ZR Fab in Phoenix (USA).

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List of affected General Parts:

BU323ZG	MJD47T4G	MJW18020G
BUB323ZG	MJD50G	NJD35N04G
BUB323ZT4G	MJD50T4G	NJD35N04T4G
BUD42DT4G	MJE13007G	NJVMJD47T4G
BUH100G	MJE13009G	NJVMJD50T4G
BUH150G	MJE15034G	NJVNJD35N04G
BUH50G	MJE18004G	NJVNJD35N04T4G
BUL45D2G	MJE18008G	SJC4196FP
BUL45G	MJE5742G	TEC0193BPF
BUX85G	MJF18004G	TIP47G
MJB5742T4G	MJF18008G	TIP48G
MJD47G	MJF47G	TIP50G